# 20A, 50V - 600V Super Fast Rectifier

## FEATURES

- AEC-Q101 qualified available
- High efficiency, low V<sub>F</sub>
- High current capability
- High surge current capability
- Low power loss
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

# APPLICATIONS

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

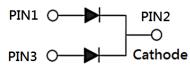
## **MECHANICAL DATA**

- Case: ITO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.82g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I <sub>F</sub>	20	A	
V <sub>RRM</sub>	50 - 600	V	
I <sub>FSM</sub>	150	A	
T <sub>J MAX</sub>	150	°C	
Package	ITO-220AB		
Configuration	Dual dies		







<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25^{\circ}C$ unless otherwise noted)										
PARAMETER	SYMBOL	SFF	SFF	SFF	SFF	SFF	SFF	SFF	SFF	UNIT
		2001G	2002G	2003G	2004G	2005G	2006G	2007G	2008G	
Marking code on the		SFF	SFF	SFF	SFF	SFF	SFF	SFF	SFF	
device		2001G	2002G	2003G	2004G	2005G	2006G	2007G	2008G	
Repetitive peak reverse voltage	$V_{RRM}$	50	100	150	200	300	400	500	600	V
Reverse voltage, total rms value	$V_{R(RMS)}$	35	70	105	140	210	280	350	420	V
Forward current	I <sub>F</sub>		20				А			
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I <sub>FSM</sub>		150				A			
Junction temperature	TJ	-55 to +150			°C					
Storage temperature	T <sub>STG</sub>	-55 to +150			°C					



# SFF2001G - SFF2008G

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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	R <sub>eJC</sub>	2.5	°C/W

ELECTRICAL SPECIFIC	ATIONS (T <sub>A</sub>	= 25°C unless otherwi	se noted)			
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
SFF2001G SFF2002G SFF2003G SFF2003G SFF2004G		1 100 T 0500		-	0.975	V
Forward voltage per diode <sup>(1)</sup>	SFF2005G SFF2006G	I <sub>F</sub> = 10A,T <sub>J</sub> = 25°C	V <sub>F</sub>	-	1.300	V
	SFF2007G SFF2008G			-	1.700	V
Reverse current @ rated V <sub>R</sub> per diode <sup>(2)</sup>		$T_J = 25^{\circ}C$	- I <sub>R</sub>	-	10	μA
		T <sub>J</sub> = 125°C		-	400	μA
Junction capacitance per diode		1MHz, V <sub>R</sub> = 4.0V	CJ	90	-	pF
Reverse recovery time		IF = 0.5A, IR = 1.0A Irr = 0.25A	t <sub>rr</sub>	-	35	ns

#### Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION				
ORDERING CODE <sup>(1)(2)</sup>	PACKAGE	PACKING		
SFF20xG	ITO-220AB	50 / Tube		
SFF20xGH	ITO-220AB	50 / Tube		

Notes:

1. "x" defines voltage from 50V(SFF2001G) to 600V(SFF2008G)

2. "H" means AEC-Q101 qualified



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

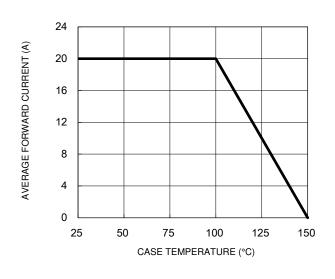
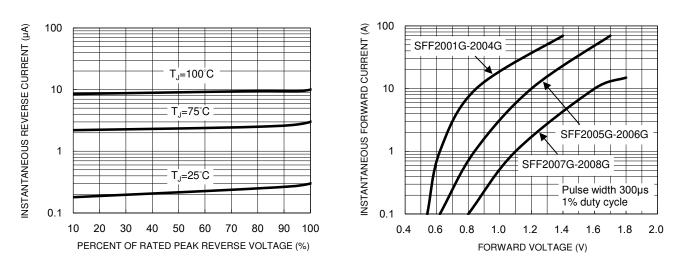


Fig.1 Forward Current Derating Curve

#### **Fig.3 Typical Reverse Characteristics**



100

90

80

70

60

50

40

1

f=1.0MHz Vsig=50mVp-p

CAPACITANCE (pF)

#### Fig.5 Maximum Non-Repetitive Forward Surge Current

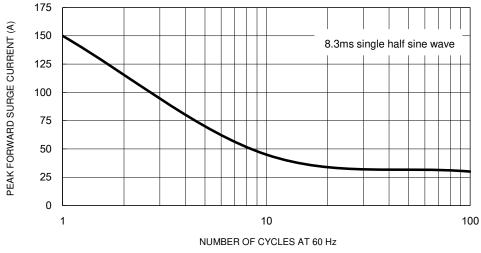
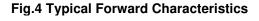


Fig.2 Typical Junction Capacitance



10

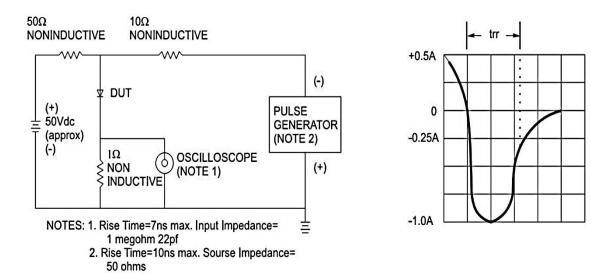
REVERSE VOLTAGE (V)

100



## **CHARACTERISTICS CURVES**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 



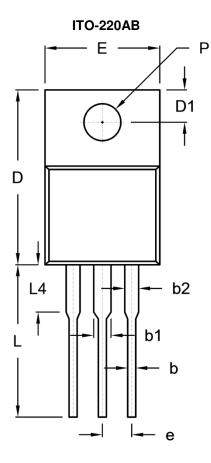
#### Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram

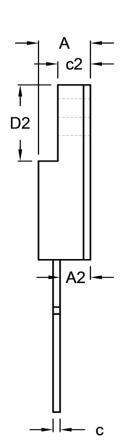


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# PACKAGE OUTLINE DIMENSIONS





DIM.	Unit (mm)		Unit	(inch)	
	Min.	Max.	Min.	Max.	
A	4.30	4.70	0.169	0.185	
A2	2.30	2.96	0.091	0.117	
b	0.50	0.90	0.020	0.035	
b1	-	1.80	-	0.071	
b2	0.95	1.45	0.037	0.057	
с	0.46	0.76	0.018	0.030	
c2	2.50	3.16	0.098	0.124	
D	14.80	15.50	0.583	0.610	
D1	2.40	3.20	0.094	0.126	
D2	6.30	6.90	0.248	0.272	
E	9.60	10.30	0.378	0.406	
е	2.41	2.67	0.095	0.105	
L	12.60	13.80	0.496	0.543	
L4	-	4.10	-	0.161	
Р	3.00	3.40	0.118	0.134	

### **MARKING DIAGRAM**

雪別 GYWW <mark>F</mark>
P/N
<b>→</b> + • • •

P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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